MOSFETs Silicon N-Channel MOS

# SSM6N67NU

#### 1. Applications

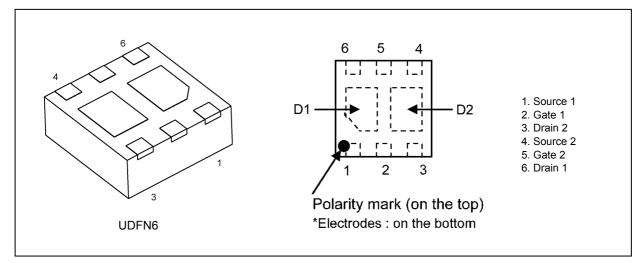
- Power Management Switches
- DC-DC Converters

### 2. Features

- (1) AEC-Q101 qualified (Note 1)
- (2) 1.8-V gate drive voltage.
- (3) Low drain-source on-resistance
  - :  $R_{DS(ON)}$  = 39.1 m $\Omega$  (max) (@V\_{GS} = 4.5 V)
    - $R_{DS(ON)}$  = 53 m $\Omega$  (max) (@V\_{GS} = 2.5 V)
    - $R_{\rm DS(ON)}$  = 82 m $\Omega$  (max) (@V\_{\rm GS} = 1.8 V)

Note 1: For detail information, please contact to our sales.

### 3. Packaging and Pin Assignment



#### Absolute Maximum Ratings (Note) (Unless otherwise specified, T<sub>a</sub> = 25 °C) (Q1,Q2 Common)

Characteristics				Symbol	Rating	Unit
Drain-source voltage				V <sub>DSS</sub>	30	V
Gate-source voltage				V <sub>GSS</sub>	12/-8	
Drain current (DC)			(Note 1)	Ι <sub>D</sub>	4	А
Drain current (pulsed)			(Note 1), (Note 2)	I <sub>DP</sub>	10	
Power dissipation			(Note 3)	PD	1	W
Power dissipation	(t ≤ 10	s)	(Note 3)	PD	2	W
Channel temperature				T <sub>ch</sub>	150	°C
Storage temperature				T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW)  $\leq$  10 ms, duty  $\leq$  1 %
- Note 3: Device mounted on an FR-4 board.(total dissipation) (25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm ,Cu pad: 645 mm<sup>2</sup>)
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 5. Electrical Characteristics

#### 5.1. Static Characteristics (Unless otherwise specified, Ta = 25 °C)(Q1,Q2 Common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	V <sub>DD</sub> = 0 V, V <sub>GS</sub> = 10/-8 V	_	_	±10	μA
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V	_		1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0 V	30		_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = -8 V	18	_	—	
Gate threshold voltage	(Note 2)	V <sub>th</sub>	V <sub>DS</sub> = 3 V, I <sub>D</sub> = 1 mA	0.40	_	1.00	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	I <sub>D</sub> = 2.0 A, V <sub>GS</sub> = 4.5 V	—	30	39.1	mΩ
			I <sub>D</sub> = 1.0 A, V <sub>GS</sub> = 2.5 V	_	37	53	
			I <sub>D</sub> = 0.5 A, V <sub>GS</sub> = 1.8 V	_	46	82	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	V <sub>DS</sub> = 3 V, I <sub>D</sub> = 2.0 A	6.0	12.0	_	S

Note 1: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

Take this into consideration when using the device.

Note 3: Pulse measurement.

#### 5.2. Dynamic Characteristics (Unless otherwise specified, Ta = 25 °C)(Q1,Q2 Common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = 15 V , V <sub>GS</sub> = 0 V, f = 1 MHz	_	310	_	pF
Reverse transfer capacitance		C <sub>rss</sub>		_	20	—	
Output capacitance		C <sub>oss</sub>		_	52	—	
Switching time (turn-on time)	(Note 1)	t <sub>on</sub>	V <sub>DD</sub> = 15 V, I <sub>D</sub> = 1.0 A,	_	26	_	ns
Switching time (turn-off time)	(Note 1)	t <sub>off</sub>	$V_{GS}$ = 0 to 2.5 V, $R_{G}$ = 4.7 $\Omega$	_	17	_	

Note 1: See chapter 5.3

#### 5.3. Switching Time Test Circuit

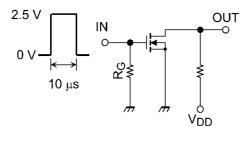


Fig. 5.3.1 Switching Time Test Circuit

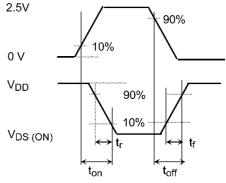


Fig. 5.3.2 Input Waveform/Output Waveform

## 5.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C) (Q1,Q2 Common)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V <sub>DD</sub> = 15 V, I <sub>D</sub> = 4.0 A,	—	3.2	—	nC
Gate-source charge 1	Q <sub>gs1</sub>	V <sub>GS</sub> = 4.5 V	_	0.5	_	
Gate-drain charge	Q <sub>gd</sub>		_	0.7	_	

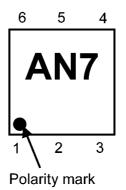


# 5.5. Source-Drain Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C) (Q1,Q2 Common)

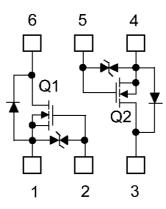
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{\text{DSF}}$	$I_{D}$ = -4.0 A, $V_{GS}$ = 0 V	—	-0.8	-1.2	V

Note 1: Pulse measurement.

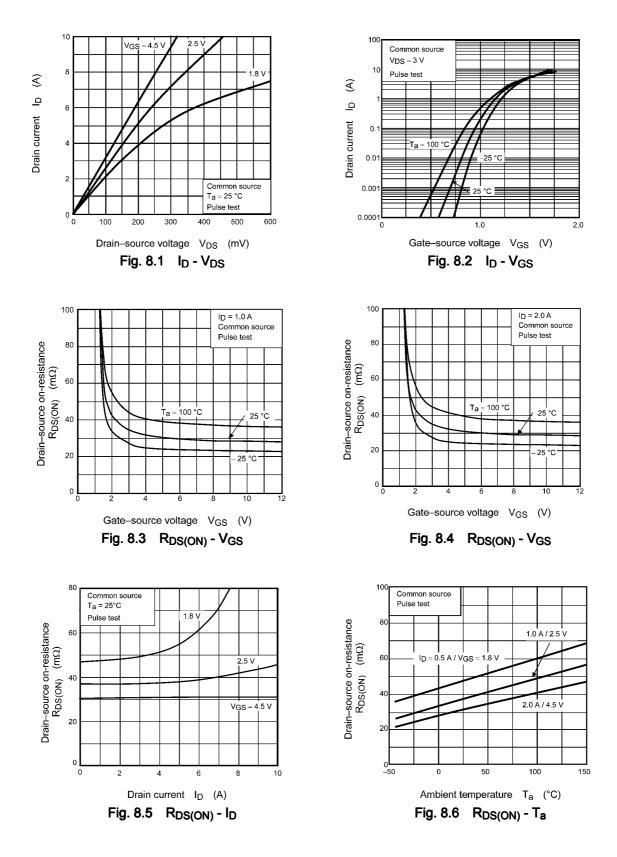
### 6. Marking

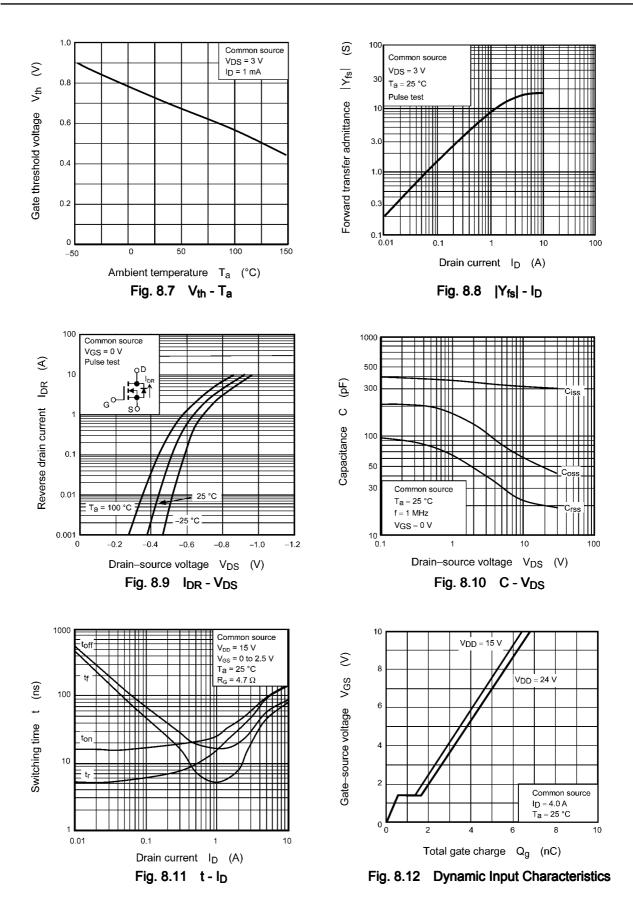


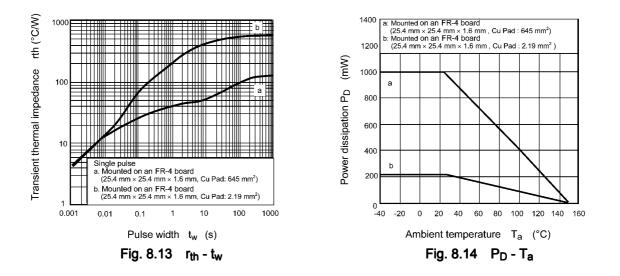
7. Internal Equivalent Circuit



### 8. Characteristics Curves (Q1,Q2 Common) (Note)







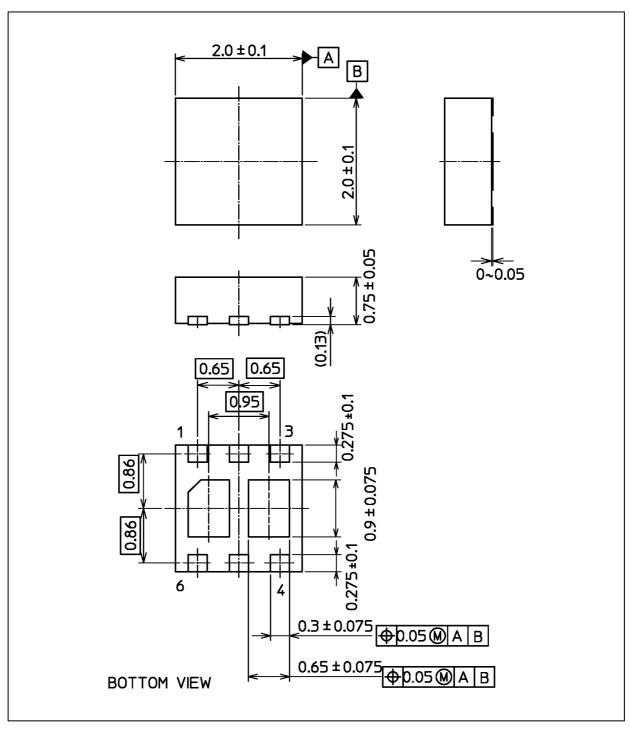
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### SSM6N67NU

#### **Package Dimensions**

Unit: mm



Weight: 8.5 mg (typ.)

Package Name(s)

Nickname: UDFN6

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